PCN Number: 2015			5060	1001		PCN Date:			6/03/2015	
Title:	Die Revision	Chang	je for select TPS3780 devices							
Customer Contact:				l Manager		Dept:			Quality Services	
Proposed 1 st Ship Date:			9/03/2015 Estimated Samp Availability:			ple			Date provided at sample request.	
Change Type:										
Assembly Site				Assembly P	rocess		Assembly Materials			
Design			☐ Electrical Specification				Mechanical Specification			
Test Site			Packing/Shipping/Labeling				Test Process			
☐ Wafer Bump Site			Wafer Bump Material				Wafer Bump Process			
☐ Wafer Fab Site			Wafer Fab Materials					Wafer	Fab Process	
			Part number change					•		
DCN Dataile										

PCN Details

Description of Change:

This notification is to announce a die revision and datasheet change to the devices listed in the Product Affected Section of this document. Communication regarding the reason for the change with the previous revision of this product was made through Texas Instruments Selective Inventory Exchange Process notice of 6/24/2014. The new Die Revision is now available and customers must submit their approval of this PCN to begin using this new Die Revision during the 90-day notification period.

The Die Revision and the datasheet number will be changing:

Current New

Die Revision	Datasheet Number	Die Revision	Datasheet Number
В	SBVS216A	C	SBVS250

Reason for Change:

Below is a summary of the design changes in Die Revision C:

- 1. OTP initialization was changed to be made more robust to VDD brownouts.
- 2. Eliminate false OUTs conditions during fast transients on the SENSE lines within min. and max. operating range.
- 3. Eliminate false OUTs conditions during fast VDD transients within its min. and max. operating range.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Die Rev designator will change as shown in the table & sample label below:

Current	New						
Die Revision [2P]	Die Revision [2P]						
В	C						

Sample product shipping label to indicate die rev location (not actual product label)







Product Affected: TPS3780ADRYR TPS3780ADRYT

Qualification Report

TPS3780ADRY, TPS3780BDRY, TPS3780CDRY, TPS3780DDRY (HNT/MIHO)
Approved 04/23/2015

Attributes	Qual Device: TP\$3780ADRY	Qual Device: TP\$3780CDRY	Qual Device: TP\$3780DDRY	Qual Device: TP\$3780BDRY	QB \$ Product: TP\$3780ADRY	QB \$ Product: TP \$386000RGP	QB \$ Product: TP\$3779ADRY	QB \$ Process: TP \$62110R \$A	QB \$ Process: TP \$72750D \$E	QB \$ Package: T \$5A 23159R \$ER	QB \$ Package: TPD45014DRY	QB \$ Package: T \$5A 21366R \$ER	QB S Package: VSP1000D SF
Assembly Site	HANA-THAILAND	HANA-THAILAND	HANA-THAILAND	HANA-THAILAND	UTAC/NSE 2	CARSEM-S	HANA-THAILAND	CAR	UTAC	HANA-THAILAND	HANA-THAILAND	HANA-THAILAND	HANA-THAILAND
Package Family	SON	SON	SON	SON	SON	QFN	SON	QFN	SON	UQFN	SON	UQFN	X2SON
Wafer Fab Site	MIHO 8	MIHO-8	MIHO-8	MIHO-8	MIHO-8	DMOS5	MIHO 8	MIHO8	MIHO8	FFAB	FFAB	FFAB	MIHO8
Wafer Fab Process	LBC7	LBC7	LBC7	LBC7	LBC7	LBC7	LBC7	LBC7	LBC7	50b10	50B10	ASLC10	LBC7

[|] Process
| GBS: Clust By, Slimitarity
| Gual Devices qualified at LEVEL1-250C: TP83750ADRY, TP83750CDRY, TP8

Qualification Results

syed,es:	Number of lots	/ Total	sample size	/ Total falled	

Туре	Test Name / Condition	Duration	Qual Device: TP\$3780ADRY	Qual Device: TP\$3780CDRY	Qual Device: TP\$3780DDRY	Qual Device: TP\$3780BDRY	QB \$ Product: TP\$3780ADRY	QB \$ Product: TP\$386000RGP	QB \$ Product: TP \$3779ADRY	QB \$ Process: TP \$62110R \$A	QB \$ Process: TP \$72750D \$E	QB \$ Package: T \$5A23159R \$ER	QB \$ Package: TPD4\$014DRY	QB \$ Package: T \$5A21366R \$ER	QB \$ Package: V\$P1000D \$F
HAST	Blased HAST, 130C/85% RH	96 Hours	-		•	-	-	-	1/77/0	3/231/0	-				-
AC	Autoclave 121C	96 Hours	-			-		1/77/0	-	3/231/0	-			3/231/0	1/77/0
TC	Temperature Cycle, - 65/150C	500 Cycles	-	-		-	-	1/77/0	1/77/0	3/231/0	-	-		3/231/0	1/76/0
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	•	-	-	-	-	-	3/231/0	-	•	•	•	1/77/0
TS	Thermal Shock, -65/150C	500 Cycles	-			-			-	3/231/0	-	-		-	
HTOL		480 Hours	-	-	-	-	-	-	-	3/231/0	-	-	-	-	-
HTOL	Life Test, 150C	300 Hours	-			-		1/77/0	-	-	1/77/0				
ELFR	Early Life Fallure Rate, 140C	48 Hours	-			-	-	-	-	3/1880/0	-	-		-	-
WBS	Ball Bond Shear	Wires	-			-			-	-	-	3/228/0	3/228/0		
WBP	Bond Pull	Wires	-								-	3/228/0	3/228/0		
PD	Physical Dimensions		-		-	-			-	-	-	3/30/0	3/30/0	-	
HBM	ESD - HBM	2000 V	-			-	1/3/0	1/3/0	1/3/0	-	1/3/0				
CDM	ESD - CDM	500 V	1/3/0			-	1/3/0	1/3/0	-	3/9/0	1/3/0				
LU	Latch-up	(per JESD78)	-		-	-		1/6/0	1/6/0	3/15/0	1/6/0	-		-	1/6/0
ED	Electrical Characterization	Per Datasheet Parameters	1/30/0	1/10/0	1/10/0	1/10/0	1/30/0	1/30/0	1/30/0	-	1/30/0	•	•	•	1/30/0
EDR	EEPROM Data Retention, 1700	420 Hours	-	-	-	-	-	1/77/0	-	-	1/77/0	-	-	-	-

EDR 100 - 100 - 400 Hours - Preconditioning was performed for Autoclars, Unbiased HAST, THE Blassed HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable — The following are requirement HTSL, options based on an activation energy of 0.74V 1.550 th Hours, 1400-430 Hours, 1500-300 Hours, and 1550-240 Hours — The following are requirement HTSL, options based on an activation energy of 0.74V 1.550 th Hours and 1700-430 Hours are 1700-430 Hours — The following are requirement for the service of the transport of the following the followin

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com